TOSHIBA Transistor Silicon NPN Triple Diffused Type

2SD2461

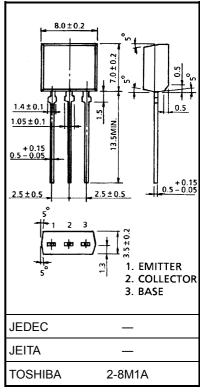
Power Amplifier Applications

Unit: mm

- High DC current gain: h_{FE} (1) = 800 to 3200 (V_{CE} = 5 V, I_{C} = 0.1 A)
- Low saturation voltage: V_{CE} (sat) = 0.3 V (typ.) (I_C = 0.5 A, I_B = 5 mA)

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V_{CBO}	60	V	
Collector-emitter voltage		V _{CEO}	60	V	
Emitter-base voltage		V _{EBO}	7	V	
Collector current	DC	I _C	2	Α	
	Pulse	I _{CP}	4		
Base current		Ι _Β	0.4	Α	
Collector power dissipation		PC	1.3	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	

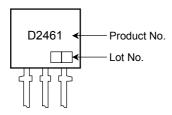


Weight: 0.55 g (typ.)

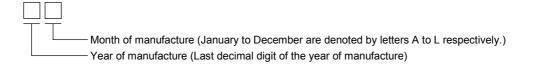
Electrical Characteristics (Ta = 25°C)

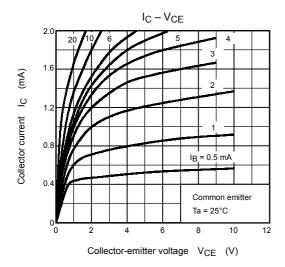
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = 60 V, I _E = 0	_	_	100	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} = 7 V, I _C = 0	_	_	100	μA
Collector-emitter breakdown voltage	V (BR) CEO	I _C = 50 mA, I _B = 0	60	_	_	V
DC current gain	h _{FE (1)}	V _{CE} = 5 V, I _C = 0.1 A	800	_	3200	
	h _{FE (2)}	V _{CE} = 5 V, I _C = 1 A	350	_	_	
Collector-emitter saturation voltage	V _{CE (sat)}	I _C = 0.5 A, I _B = 5 mA	_	0.3	1.0	V
Base-emitter voltage	V_{BE}	V _{CE} = 5 V, I _C = 0.5 A	_	0.7	1.0	V
Transition frequency	f _T	V _{CE} = 5 V, I _C = 0.5 A	_	17	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz	_	30	_	pF

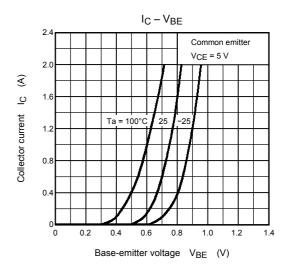
Marking

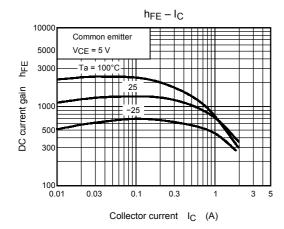


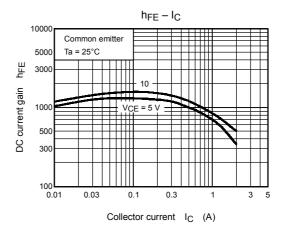
Explanation of Lot No.

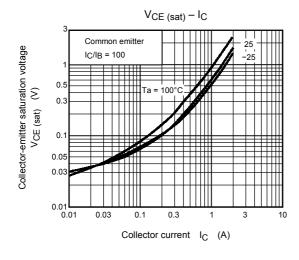


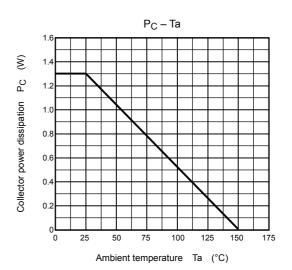




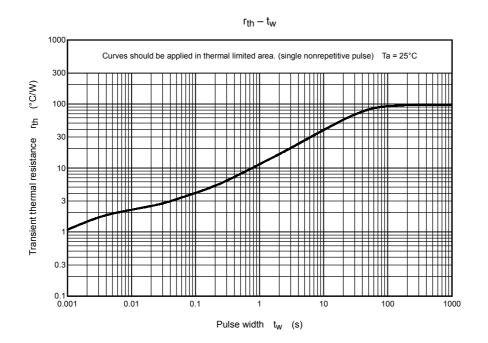


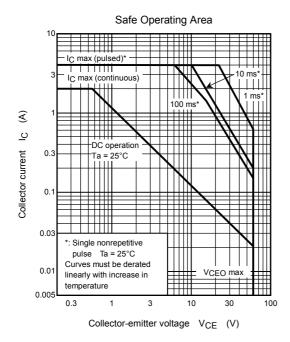






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